- 5. Camilo F et al. *Nature* **442** 892 (2006)
- 6. Goldreich P, Julian W H Astrophys. J. 157 869 (1969)
- Gurevich A V, Istomin Ya N Zh. Eksp. Teor. Fiz. 89 3 (1985) [Sov. Phys. JETP 62 1 (1985)]
- Istomin Ya N, Sobyanin D N Pis'ma Astron. Zh. 33 740 (2007) [Astron. Lett. 33 660 (2007)]
- Beskin V S, Gurevich A V, Istomin Ya N Physics of the Pulsar Magnetosphere (Cambridge: Cambridge Univ. Press, 1993)
- 10. Kramer M et al. *Science* **312** 549 (2006)
- 11. Gurevich A V, Istomin Ya N Mon. Not. R. Astron. Soc. **377** 1663 (2007)

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## Multichannel propagation and scattering of phonons and photons in low-dimension nanostructures

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#### 1. Introduction

Recent major achievements in the research and development of technologically and functionally advanced materials have markedly increased research interest in the generation and propagation of coherent acoustic phonons in quasi-onedimensional superstructures (including those with 'acoustic nanocavities' [1]), nanowires, and nanorods [2]. Of much importance in terms of potential applications is the study of phonon heat transfer in low-dimension systems — for example, through a solid-solid microcontact [3]. The search for technologically feasible materials for thermoelectric transducers lent very topical significance to the recent experimental finding that silicon nanowires with rough surfaces have a much lower thermal conductivity than their smooth-surface counterparts and bulk silicon [4-6]. Furthermore, the phonon contribution to the thermal conductivity of singlecrystal silicon nanowires with a diameter of less than 50 nm approaches the limiting value found for amorphous silicon, something which current theories cannot explain [5]. Also, the molecular dynamics modeling of the thermal conductivity of diamond nanorods whose surfaces are coated with hydrogen with attached phenyl groups has shown that the thermal conductivity of nanorods is much less than that of bulk crystals [7].

This talk describes and discusses several examples of the so-called multichannel propagation and scattering of phonons and photons, two processes which can contribute to the phonon and photon characteristics, both dynamic and kinetic, of low-dimension systems.

The important thing about the multichannel propagation of phonons or photons is that there are several 'parallel' paths along which propagation is effected, between which both constructive and destructive interference can take place. Path-to-path interference occurring during multichannel propagation in a low-dimension system results in the transmission, reflection, and/or absorption coefficients generally having an asymmetric (non-Lorentzian) line shape as a function of the phonon (photon) frequency.

An asymmetric absorption line shape was first described by Fano [8] in his study of inelastic autoionization resonances in atoms and has been interpreted as due to discrete resonances interfering with the surrounding continuum of

'background' states. Although Fano type asymmetric absorption profiles have been discovered in many atomic systems (see, for example, Ref. [9]), they are not exclusive to them alone and have also been detected in doped semiconductor materials (the absorption [10] and Raman scattering [11] spectra taken from impurities), as well as in bulk intrinsic semiconductor GaAs and semiconductor superlattices [12, 13], and in quantum wells [14]. In the context of electron transport, conductivity as a function of applied voltage or gate voltage has been observed to exhibit asymmetric peaks in quantum dots with few electron levels [15, 16], crossed carbon nanotubes [17], and quantum wires with an attached 'lateral' quantum dot [18, 19]. The electron Fano effect in a quantum dot on one arm of an Aharonov-Bohm interferometer can interact with the Aharonov-Bohm effect [20, 21] and with Kondo correlations in the quantum dot [22]. For photons, the clearest manifestation of the Fano effect is the asymmetrically shaped line of the photon transmission coefficient through a two-dimensional system of local (plasmonic or opticalphonon) resonances [23, 24] or through a layer of a transparent material with a periodic arrangement (twodimensional lattice) of holes [25, 26].

The phonon analogue of the Fano effect was first described in Ref. [27] and Ref. [28] independently. Reference [27] studied, in particular, the passage of a long acoustic wave (acoustic phonon) through a crystal two-dimensional (2D) defect with a complex structure. A peculiarity in considering such a 2D defect in crystal consisted in accounting for not only the interaction between the neighboring atomic layers closest to the defect but also the direct interaction of the lattice matrix rims through the defect monolayer. In an atomic model of the 2D defect this corresponds to the interaction between nonclosest neighbors. Reference [27] predicted that this essentially monolayer defect characterized by weak local force bondings of both nearest and more distant neighbors can fully reflect in a resonant manner acoustic phonons with wavelengths much larger than the physical thickness of the defect. From the viewpoint of the Fano effect interpretation, the reason for the anomalously strong reflection of an acoustic wave is the destructive interference between two phonon wave paths: through a local oscillator (or through the local bondings of the nearest neighbors) and through the local force bondings of the nonclosest neighbors, bypassing around the local oscillator. A further prediction of Ref. [27] was that a phonon undergoes total resonant absorption (total nonreflection and total nontransmission) at the boundary of a crystal 2D defect with a complex structure. As noted in Ref. [27], a normally incident, longwave acoustic phonon cannot suffer anomalously strong resonant reflection (or absorption) by a laterally uniform layer of the material (see, for example, the well-known monograph [29]); this can only happen in the acoustics of composite materials. What a laterally uniform layer can only do is resonantly increase the phonon transmission coefficient under Fabry-Perot resonance conditions, thus demonstrating the phonon analogue of the resonant bleaching effect. The interaction of the matrix rims directly through the defect layer is equivalent to the lateral nonuniformity of a two-dimensional defect. Introducing this additional local interaction can also be regarded as effectively taking into account that impurities do not always fill the entire surface of a crystal 2D defect, i.e., impurity atoms can alternate in the plane of the defect with matrix atoms or, alternatively, there may be two or more types of impurities in a 2D defect (Fig. 1).



Figure 1. Three possible 1D lattice models describing the multichannel propagation of phonons through a lattice region containing a local defect.

Reference [28] drew an analogy between the scattering of electrons and the scattering of phonons and calculated numerically the phonon transmission coefficients with an asymmetric line shape for a quasi-one-dimensional multichannel waveguide consisting of a strip of oscillator chains connected in parallel. However, the oscillatory phenomena occurring in quasi-one-dimensional systems of oscillator chains were not generalized to the case of phonons propagating and undergoing a scattering in real 3D systems [28], such as that considered in Ref. [27] 2D defect of complex structure in a 3D crystal.

The later work [30] was the first to study experimentally the acoustic properties of a so-called 'locally resonant' material, a 3D lattice of rubber-coated steel balls embedded in a solid epoxy resin matrix. It was shown that at frequencies close to the natural frequency of a steel ball in a solid matrix, a 'monolayer' of such composite material is capable of essentially totally reflecting, in a resonant manner, the acoustic wave with a wavelength nearly two orders of magnitude larger than the physical thickness of the layer. It was shown, further, that the anomalously strong resonance reflection of an acoustic phonon from a composite layer is essentially unaffected by the irregular (not strictly 2D periodical) distribution of identical elastic-wave scatterers in the solid matrix. Both the material used and the resonance phenomenon observed in Ref. [30] can be given an immediate interpretation in terms of the model posed in Ref. [27] if the layer of steel balls in a solid matrix is regarded as a crystal 2D defect formed by 'weakly coupled' impurities, and the material of the matrix between 'local resonators' as a force bonding through the composite layer, bypassing around the resonators (Fig. 1a). It is significant that in both Ref. [27] and Ref. [30] the above effects were given a correct theoretical description and experimentally studied without using any analogies with the Fano effect. That acoustic phenomena in locally resonant materials can be interpreted in terms of a phonon analogue of the Fano effect was first brought to attention in Refs [31, 32] (note that, however, the analogy itself added nothing either to the theoretical description or to the experimental investigation of the acoustic phenomena in question). A two-dimensional system of thin-walled elastic hollow cylinders is, as shown in Ref. [33], another example where the peculiarities of the resonant propagation of acoustic waves are most naturally explained using an analogy with the Fano effect.

# 2. Multichannel scattering of acoustic phonons from a crystal two-dimensional defect

To macroscopically describe the scattering of a long-wave acoustic phonon from a crystal 2D defect requires that the form (and number) of boundary conditions for surface bulk strains ( $\sigma_{zi} = \lambda_{zilm} u_{lm}$ ) and elastic displacements ( $u_i$ , i = 1, 2, 3) be specified on the surface of the defect (z = 0plane). If the interface between two solids is sharp, then all that is needed is that these quantities be continuous (see Ref. [34]). In the general case, both the surface strains and elastic displacements exhibit discontinuities at the surface of a crystal 2D defect (see Ref. [35]). Denoting by N the number of types of atoms residing in the plane of the 2D defect, the simplest generalization of the multichannel propagation model posed in Ref. [27] reduces to the following dynamic equations on the surface of the defect:

$$\sigma_{zi}^{(1)} = \sum_{l=1}^{N} A_{ik}^{(l)} (u_k^{(ls)} - u_k^{(1)}) - \varrho \, \frac{\partial^2 u_i^{(1)}}{\partial t^2} \,, \tag{1}$$

$$\sigma_{zi}^{(2)} = \sum_{l=1}^{N} A_{ik}^{(l)} (u_k^{(2)} - u_k^{(ls)}) + \rho \, \frac{\partial^2 u_i^{(2)}}{\partial t^2} \,, \tag{2}$$

$$\rho_{\rm s}^{(l)} \, \frac{\partial^2 u_i^{(ls)}}{\partial t^2} = A_{ik}^{(l)} (2u_k^{(ls)} - u_k^{(1)} - u_k^{(2)}) \,, \tag{3}$$

where the *z*-axis is directed from medium 1 to medium 2;  $u_i^{(1,2)}$ and  $u_i^{(k)}$  are the macroscopic (averaged) displacements of the matrix rims and surface atoms of the *l* type; the symmetric tensor  $A_{ik}^{(l)}$  describes the interaction of the matrix rims with the surface atoms of the *l* type, while  $\rho_s^{(l)}$  and  $\rho$  are the surface densities of *l* type atoms and of atoms in the near-surface layers [the latter density should only be considered if it is large compared to the average 'bulk' density (see Fig. 4 below)]. For N = 2 and  $\rho_s^{(2)} = 0$  (or  $\rho_s^{(2)} \ll \rho_s^{(1)}$ ), equations (1)–(3) are reduced to those obtained in Ref. [27]:

$$\sigma_{zi}^{(1)} = A_{ik} \left( u_k^{\rm s} - u_k^{(1)} \right) + B_{ik} \left( u_k^{(2)} - u_k^{(1)} \right) - \varrho \frac{\partial^2 u_i^{(1)}}{\partial t^2} , \quad (4)$$

$$\sigma_{zi}^{(2)} = A_{ik} \left( u_k^{(2)} - u_k^{\rm s} \right) + B_{ik} \left( u_k^{(2)} - u_k^{(1)} \right) + \varrho \frac{\partial^2 u_i^{(2)}}{\partial t^2} \,, \quad (5)$$

$$\rho_{\rm s} \, \frac{\partial^2 u_i^{\rm s}}{\partial t^2} = A_{ik} \left( 2u_k^{\rm s} - u_k^{(1)} - u_k^{(2)} \right), \tag{6}$$

where  $u_i^s = u_i^{(1s)}$ ,  $\rho_s = \rho_s^{(1)}$ ,  $A_{ik} = A_{ik}^{(1)}$ , and the tensor  $B_{ik} = (1/2) A_{ik}^{(2)}$  describes the 'direct interaction' between the matrix rims via the defect layer. When the normal to the surface of the 2D defect coincides with a symmetry axis of the crystal and when this is the only wave propagation direction of interest, then in the simplest case of interaction between only nearest neighboring atoms in the bulk of the crystal the 3D equations (1)–(3) and (4)–(6) can be reduced to 1D oscillator chain models (Figs 1a and 1b for the case of N = 2). Notice that in the latter of these models (Fig. 1b) the local force bondings near the defect correspond to the situation in which both the nearest and more distant neighbors interact. As can be seen by comparing Figs 1a and 1b, the latter force bondings through the matrix, bypassing around the defect atom.

The long-wave approximation allows a direct correspondence to be made between elasticity theory equations (4)-(6) (used, for example, to describe the interaction of a

*z*-propagating longitudinal phonon with a 2D defect) and the 1D lattice model of this 2D defect, presented in Fig. 1b:

$$\sigma_{zz} = \lambda_{zzzz} \frac{\partial u_z}{\partial z} \to \frac{c(u_{n+1} - u_n)}{a^2}, \qquad (7)$$

and between all the parameters in both descriptions:  $\lambda_{zzzz} \rightarrow c/a$ ,  $A \rightarrow c_1/a^2$ ,  $B \rightarrow c_2/a^2$ ,  $\rho \rightarrow m^*/a^2$ , and  $\rho_s \rightarrow m_1/a^2$ , where *a* is the 1D lattice spacing. Below we will use the simple 1D lattice models of Fig. 1 as an example to describe the most interesting aspects of the multichannel propagation of phonons through a crystal 2D defect.

For a 2D defect coinciding with the n = 0 plane, the solution of the corresponding linear lattice equations for the planes  $n \le -2$  and  $n \ge 2$  are assumed to be of the form

$$u_n = \exp(ikan - i\omega t) + r \exp(-ikan - i\omega t), \ n \le -2, \ (8)$$

$$u_n = t \exp\left(\mathrm{i}kan - \mathrm{i}\omega t\right), \quad n \ge 2, \tag{9}$$

where  $\omega$  and k are the frequency and wave number of the incident acoustic phonon, and r and t are the amplitude reflection and transmission coefficients, respectively. The reflection (R) and transmission (T) coefficients are respectively defined as  $R = |r|^2$  and  $T = |t|^2$ . In the absence of dissipation, the condition to be satisfied is the conservation of energy for the incident acoustic phonon, T + R = 1, a condition we always check when carrying out calculations. Equations of motion for three planes -n = -1, n = 0, and n = 1 — are determined either by the long-wave approximation equations (1)-(3) [alternatively, (4)-(6)] or by the corresponding discrete lattice equations [due to the presence of correspondence (7) in the long-wave limit]. The phonon dispersion relation in the lattice under study is given by  $\omega = \omega_{\max} \sin(ka/2)$  (where  $\omega_{\max} = 2\sqrt{c/m}$ ), which is usual for a 1D monatomic model with the nearest neighbor interaction.

For the fault of direct interaction between the defect rims,  $c_2 = 0$ , the presence of a weakly coupled defect, for example, with  $c_1 = 0.07c$  and  $m_1 = m^* = m$ , brings about the resonant passage of the phonon through the system at  $\omega =$  $\omega_0 \approx \sqrt{2c_1/m_1} \ll \omega_{\text{max}}$  against the background of its transmission decreasing as a whole with increasing frequency [36] (Fig. 2a). This transmission resonance is analogous to the acoustic Fabry-Perot resonance at a monolayer of a 'soft' laterally uniform material embedded in a more 'rigid' medium. Allowing for a second phonon propagation channel, one with  $c_2 \ge c_1$  (and with or without a matrix atom with  $m_2 = m$  or  $m_2 = 0$ , see Fig. 1a), results in our obtaining, instead of the total resonance transmission of the phonon, its total resonance reflection at the same frequency  $\omega_0 \approx$  $\sqrt{2c_1/m_1}$  (Fig. 2c, corresponding to the model of Fig. 1a with  $c_2 = 0.9c$ ,  $c_1 = 0.07c$ , and  $m_2 = m_1 = m^* = m$ ). This effect, first described in Ref. [27], provides the clearest evidence for the influence of an additional channel on the propagation and scattering of phonons in low-dimension multichannel systems and nanostructures. Because for a weakly coupled defect the resonance frequency is low,  $\sqrt{2c_1/m_1} \ll \omega_{\text{max}} = 2\sqrt{c/m}$ , the wavelength of a totally reflected phonon is much larger than the physical width  $d \approx 2a$  of the nanodefect.

As noted earlier and as is clear from the properties of the systems discussed, a phonon incident normal to a 2D defect can only suffer total reflection from a laterally nonuniform and 'locally resonant' composite layer. For an intermediately

**Figure 2.** Energy transmission coefficients as functions of the normalized frequency  $\omega/\omega_{\text{max}}$  for phonons passing through a lattice 2D defect. The one-dimensional projection of the defect corresponds to the model shown in Fig. 1a with  $m_1 = m^* = m$  and (a)  $c_1 = 0.07c$ ,  $c_2 = 0$ , (b)  $c_2 = 4c_1 = 0.28c$ ,  $m_2 = 0$ , and (c)  $c_1 = 0.07c$ ,  $c_2 = 0.9c$ ,  $m_2 = m$ .

strong force bonding relevant to the direct interaction between lattice matrix rims, the frequency dependence of the transmission coefficient acquires asymmetric form, as is characteristic of the Fano effect (Fig. 2b, corresponding to the Fig. 1a model with  $c_2 = 4c_1 = 0.28c$ ,  $m_1 = m^* = m$ ,  $m_2 = 0$  or to the Fig. 1b model with  $c_2 = 2c_1 = 0.14c$ ,  $m_1 = m^* = m$ ). In this case, the phonon transmission coefficient takes both zero and unity values at frequencies close to  $\omega_0$ .

The same features are seen in the passage of phonons through a nanodefect in a quasi-one-dimensional waveguide with a 'lateral' oscillator (or a chain thereof) attached to it to serve as a 'phonon lead' (Fig. 1c). For a given weak force bonding in the phonon lead,  $c_1 \ll c$ , the transmission coefficient for a given weak force of the 'longitudinal bonding' of the defect,  $c_d \ll c$ , has one or several *transmission resonances* 



of the Fabry–Perot type. For a relatively strong longitudinal bonding of the defect,  $c_d \approx c \gg c_l$ , the transmission coefficient has one or several *reflection resonances* in the low frequency range against the background of almost total transmission for the rest of the frequencies. In particular, if a phonon lead with one, two, or three series-connected, identical, weakly coupled links for each of which  $m_l = m$ and  $c_l \ll c$  is attached to one site of the 1D lattice with  $m_d = m$ and  $c_d = c$ , then the propagation of a long-wave phonon through such a defect is characterized by the presence of one, two, or three resonance frequencies, respectively, at which total reflection occurs (see Fig. 3 for the case of  $c_l = 0.1c$ ). For each such resonance, the second phonon propagation channel, whose destructive interference with the channel along the 1D crystal results in the complete suppression of



**Figure 3.** Energy transmission coefficients versus frequency for phonons passing through a 1D waveguide containing a lateral chain depicted in Fig. 1c with one (a), two (b), and three (c) identical links for the case of  $m_d = m_l = m$ ,  $c_d = c$ , and  $c_l = 0.1c$ .

transmission, is one of the natural vibrational modes of the phonon lead, the total number of the modes being determined by the number of links in the lead. The 1D crystal model with phonons lead will be used in what follows to simulate the phonon thermal conductivity of nanowires with dynamically rough surfaces.

Multiple phonon transmission zeros are also found in a 1D lattice (or a crystal 2D defect) with several parallel propagation channels similar to those in Fig. 1a. In the general case, N transmission channels can produce N - 1 total reflection resonances.

The large mass  $m^*$  of near-surface atoms and the correspondingly large near-surface density  $\rho$  in Eqns (1)–(6) are further crucial factors for the resonant transmission of a phonon through 2D defects of the crystal whose 1D lattice models are shown in Fig. 1 [27]. In particular, the simplest 1D model depicted in Fig. 1b accounts for the presence of one or two resonance transmission peaks through two or three layers of strongly bounded 'heavy' impurity atoms, when  $c_1 = 0$ ,  $c_2 = c, m^* = 5m \text{ and } c_1 = c, c_2 = 0, m^* = m_1 = 5m, \text{ respec-}$ tively (Figs 4a and b). In other words, N strongly coupled dense layers produce N-1 Fabry-Perot type phonon transmission resonances with a characteristic frequency (or interfrequency interval)  $\omega_{\rm hl} \approx \sqrt{2c/m^*}$  [unlike N weakly coupled layers leading to N phonon transmission resonances of the Fabry-Perot type (Fig. 2a)]. As far as electron transport in the strongly coupled 1D lattice model is concerned, the reader is referred to papers [37, 38] for a discussion of the resonance transparency of a pair of equalenergy sites (dimer) and how this transparency influences the delocalization of electron states in random dimer lattices and, in particular, in conducting polymers.

An additional resonance in transmission through the vibrating 'dimer' of strongly coupled dense layers can produce a 'double' transmission resonance (double Fano type resonance), in which the natural frequencies of two strongly coupled dense outer layers coincide with those of a weakly coupled inner layer (Fig. 1b). In this case, a narrow reflection resonance (a transmission minimum) is observed against a background of transmission resonance (Fig. 4c). However, a particularly pronounced effect can be observed in the case of natural vibrations undergoing finite dissipation under double-resonance conditions; this is the total surface absorption of an incident phonon by a lattice 2D defect [27], an effect in which the transmission and reflection coefficients simultaneously tend to zero and the surface absorption  $A_{\rm s} = 1 - T - R$  approaches unity (Fig. 4d). Phenomenologically, the dissipation of vibrations can be introduced through the imaginary parts of the constants of local force bondings  $c_1$ and  $c_2$ , which are assumed to be proportional to the frequency and small compared to the real parts of the corresponding force constants. For total surface absorption,  $A_{\rm s} \approx 1$ , the following conditions must be satisfied [27]:

$$\omega_0 = \sqrt{\frac{2c_1 + c_1^2/c_2}{m_1}} = \sqrt{\frac{c_1 + 2c_2}{m^*}},$$
(10)

$$\frac{m^*}{m_1} = \frac{c_2}{c_1}, \quad \text{Im} \left(c_1 + 2c_2\right) = 2c \frac{\omega_0}{\omega_{\text{max}}}.$$
 (11)

Figure 4d displays the transmission, reflection, and surface absorption coefficients which are calculated for the following parameters of a 2D defect as modelled by Fig. 1b:  $c_1 = c(0.2 - i0.0165\omega/\omega_{max}), c_2 = c(1 - i\omega/\omega_{max}), m^* = 5m$ ,



**Figure 4.** Energy transmission coefficients versus frequency for phonons passing through a 2D lattice defect containing two (a), (c) – (e) and three (b) highdensity atomic layers and corresponding to the one-dimensional model of Fig. 1b with (a)  $m^* = 5m$ ,  $c_1 = 0$ ,  $c_2 = c$ , (b)  $m^* = m_1 = 5m$ ,  $c_1 = c$ ,  $c_2 = 0$ , and (c)  $c_1 = 0.2c$ ,  $c_2 = c$ ,  $m^* = 5m$ ,  $m_1 = m$ . (d) Energy transmission (*T*), reflection (*R*), and surface absorption ( $A_s = 1 - T - R$ ) coefficients as functions of frequency for a 2D defect with  $c_1 = c(0.2 - i0.0165\omega/\omega_{max})$ ,  $c_2 = c(1 - i\omega/\omega_{max})$ ,  $m^* = 5m$ , and  $m_1 = m$ . (e) Energy amplification coefficient  $A_s = T + R - 1$  as a function of frequency for a 2D defect with  $c_1 = c(0.2 + i0.0168\omega/\omega_{max})$ ,  $c_2 = c(1 + i0.92850\omega/\omega_{max})$ ,  $m^* = 5m$ , and  $m_1 = 0.88m$ . (f) Energy loss coefficient  $A_1 = 1 - R_1 - T_1$  as a function of frequency for a 1D waveguide for reflection from a single phonon lead (Fig. 1c) with an effective mass (18) and the dimensionless coupling parameter  $f = c_1/c = m_1/m = 0.1$ .

 $m_1 = m$ , and which agree with the analytical prediction following from formulas (10) and (11).

Based on the effect of the total absorption of an acoustic phonon by a double resonance layer — an effect similar to the total absorption of a flux of photons by resonant atoms in optics — it is, in principle, possible to build a phonon laser working by amplifying a radiation-stimulated (with  $|A_s| \ge 1$ ) phonon field propagating through a preliminary excited double resonance layer. (This amplification mechanism is different from the mechanism studied in Ref. [39], by which acoustic phonons are resonantly emitted from a weakly coupled semiconductor superlattice.)

Because stimulated radiation corresponds to the case of a 'negatively absorbed' phonon field, values of  $|A_s| \ge 1$  can be reached by changing the sign of the imaginary parts of the force bonding constants  $c_1$  and  $c_2$ . Figure 4e exhibits the resonant value of energy amplification coefficient  $A_s \sim 2 \times 10^{11}$ , which is achieved at a double resonance layer (Fig. 1b model) with  $c_1 = c(0.2 + i0.0168\omega/\omega_{max})$ ,  $c_2 = c(1 + i0.92850\omega/\omega_{max})$ ,  $m^* = 5m$ , and  $m_1 = 0.88m$ . With this

large numerical value of the amplification coefficient, it is hopeful that a system of appropriate double vibrational layers will indeed be able to produce a strengthened phonon field in the sample.

## **3.** Acoustic phonon scattering in a quasi-one-dimensional waveguide with surface phonon leads

This section will discuss a phonon scattering model by a system of surface phonon leads in a quasi-one-dimensional waveguide. In this model it is assumed that an (infinitely) long oscillator chain with a small dimensionless coupling coefficient  $f \ll 1$  is attached to each atom in the 1D crystal (phonon waveguide), when  $c_1 = fc$ ,  $m_1 = fm$  (Fig. 5). Phonon propagating along the waveguide excites vibrations in a lead, which propagate along the lead and, most importantly, do not return to the waveguide as a coherent phonon. We will apply this model to describe phonon scattering by a 'dynamic roughness' on the surface of a quasi-one-dimen-

**Figure 5.** Schematic of the one-dimensional waveguide with identical phonon leads attached to each site as an extension of the one-dimensional model of Fig. 1c with a single lead defect.

sional waveguide and how this scattering influences the phonon thermal conductivity of nanowires. In the layer of a dynamic roughness there occur random intersections and contacts between different phonon leads, which, in turn, results in a phonon suffering random scatterings in its travel along a lead and, correspondingly, not returning to the waveguide as a coherent wave (in-phase with the generating phonon in the waveguide). In the dynamic lattice model, a dynamic roughness can be described by a random arrangement of vacancies and vacancy clusters in the lattice layer of atoms, which surrounds the waveguide. The dimensionless coupling coefficient f < 1, a characteristic of dynamic coupling between the 'single-crystal' waveguide and the disordered waveguide in the surface layer, can be related to the dimensionless vacancy 'filling factor' in this layer.

As seen from Fig. 3, with increasing N (the number of links in a lead), the minimum total reflection frequency decreases (as  $\omega_N \sim \sqrt{c_1/m_1} \pi/N$  for  $N \ge 1$ ), the total reflection frequencies condensing in the low-frequency region. For  $N \ge 1$ , this is equivalent to the formation of an effective quasigap in the low-frequency vibrational spectrum of such a quasi-one-dimensional system: in the quasigap, vibrations become strongly damped and their passage through a finite length system is hindered, correspondingly decreasing the phonon thermal conductivity of the system.

We assume that displacements in the *n*-th phonon lead take the form of a wave outgoing from the waveguide and carrying its vibrational energy away:

$$u_{m,n} = A_{1,n} \exp\left[-\mathrm{i}\omega t + \mathrm{i}k_{\perp}a(m-1)\right], \qquad (12)$$

where m = 1, 2, ... are the atomic numbers in the link counted in the direction away from the waveguide, and  $k_{\perp}$  is the wave number along the waveguide, which is related to the wave frequency by the relationship  $\omega = 2\sqrt{c_1/m_1} \sin(k_{\perp}a/2)$ . In the low-frequency and long-wave limit  $k_{\perp}a \ll 1$ , we find  $k_{\perp}a \approx \omega \sqrt{m_1/c_1}$ . Using formula (12), we obtain

$$\left[m\omega^{2}-4c\sin\left(\frac{k_{\parallel}a}{2}\right)^{2}\right]\left[m_{1}\omega^{2}-c_{1}+c_{1}\left(\exp\left(ik_{\perp}a\right)-1\right)\right]$$
$$=c_{1}\left[m_{1}\omega^{2}+c_{1}\left(\exp\left(ik_{\perp}a\right)-1\right)\right]$$
(13)

for the dispersion of a phonon with the wave number  $k_{\parallel}$  along a quasi-one-dimensional waveguide with surface leads. From this, passing to the low-frequency (long-wave) limit  $(k_{\parallel}, k_{\perp}) a \ll 1$ , when  $k_{\perp} a \approx \omega \sqrt{m_{\rm l}/c_{\rm l}}$ , we arrive at the equation for the complex wave number  $k_{\parallel}$  of a damping phonon:

$$k_{\parallel}^2 a^2 = \omega^2 \, \frac{m + m_{\rm l}}{c} + {\rm i}\omega \, \frac{\sqrt{m_{\rm l} c_{\rm l}}}{c} \,. \tag{14}$$

This equation implies that in the frequency range  $\omega \gg \omega^* \equiv \sqrt{m_l c_l}/(m + m_l)$  phonons are weakly damped (the imaginary part of the phonon wave vector is small and frequency-independent) and propagate ballistically:

$$k_{\parallel}a = \omega \sqrt{\frac{m+m_{\rm l}}{c}} + \frac{{\rm i}}{2} \sqrt{\frac{m_{\rm l}c_{\rm l}}{(m+m_{\rm l})\,c}}.$$
 (15)

In the low-frequency limit,  $\omega \ll \omega^*$ , phonons are strongly damped:

$$k_{\parallel}a = \frac{1+i}{\sqrt{2}} \sqrt{\omega} \, \frac{(m_{\rm l}c_{\rm l})^{1/4}}{\sqrt{c}} \,, \tag{16}$$

and propagate diffusively in accordance with the equation  $i\omega = D_{\rm ph}k_{\parallel}^2$  comprising the diffusion coefficient

$$D_{\rm ph} = \frac{ca^2}{\sqrt{m_{\rm l}c_{\rm l}}} = V_{\rm ph}l_{\rm ph}\,,\tag{17}$$

where  $V_{\rm ph} = a\sqrt{c/m}$  is the velocity of long-wave phonons, and  $l_{\rm ph} = a\sqrt{mc/m_lc_l} \equiv a/f$  is the phonon mean free path. This latter is also defined as half the inverse imaginary part of the ballistic phonon wave vector as given by formula (15). In conformity with the definition of the absorption coefficient of an acoustic phonon [34], twice the imaginary part of the wave vector defines the absorption coefficient of phonon energy. Consideration of the energy loss coefficient  $A_l = 1 - R_l - T_l$  of a phonon on a single phonon lead yields a similar estimate for the phonon mean free path. The presence of a phonon lead is tantamount to the renormalization of the mass  $m_l$  in a waveguide with a single lateral oscillator (Fig. 1c). In this case, the mass  $m_l$ is replaced by a complex effective mass

$$m_1^{\text{eff}} = m_1 + \frac{c_1}{\omega^2} \left[ \exp\left(ik_{\perp}a\right) - 1 \right]$$
$$\equiv f \left[ m + \frac{c}{\omega^2} \left( \exp\left(ik_{\perp}a\right) - 1 \right) \right]. \tag{18}$$

Figure 4f presents the frequency dependence of the energy loss coefficient  $A_1$  in a one-dimensional waveguide for reflection from a single 'lateral defect' with the effective mass (18) for the case of f = 0.1. It is seen that  $A_1 \approx f$  over a very wide frequency range, including low frequencies. Therefore, if such scatterers are arranged in the waveguide with a spatial period a, the mean free path of a phonon in respect to energy is estimated to be  $l_{\rm ph} \approx a/f$ , which is in line with formula (17).

Let us now estimate the dimensionless dynamic coupling coefficient  $f \ll 1$  between a phonon lead and a waveguide. For a rod with a circular or rectangular cross section, this parameter can be estimated as the ratio of the number of force atomic bonds in the rough surface layer to that in the undistorted portion of the waveguide, i.e., as  $f \sim \delta/D$ , where  $\delta \sim \sqrt{h^2}$  is the root-mean-square roughness height, and *D* is the nanowire diameter. The phonon mean free path is then estimated to be

$$l_{\rm ph} \approx \frac{a}{f} \sim \frac{a}{\delta} D \ll D \,. \tag{19}$$

From formulas (17) and (19) we obtain the following estimate for the phonon thermal conductivity  $\varkappa_{ph}$  of a

nanowire with a dynamically rough surface:

$$\varkappa_{\rm ph} \sim C_{\rm ph} D_{\rm ph} \sim C_{\rm ph} V_{\rm ph} \frac{a}{\delta} D,$$
(20)

where  $C_{\rm ph}$  is the phonon specific heat.

Thus, phonon scattering from dynamic roughnesses in nanowires decreases the phonon mean free path (and hence the phonon contribution to thermal conductivity) as the parameter  $a/\delta$  decreases. Because  $a \approx 0.54$  nm in silicon and the root-mean-square roughness height varied in the range 1-5 nm [5], the parameter  $\delta/a$  falls within the range 2-10. This ratio of the phonon mean free paths (and thermal conductivity) in smooth and rough surface nanowires (with  $\delta \sim a$  and  $\delta \gg a$ , respectively) is consistent with the experimental value of 5-8 for the corresponding factor [5].

What seems contradictory about estimate (19) is that because of scattering from the surface the phonon mean free path turns out to be less than the diameter of the sample: it is usually considered that  $l_{ph} = D$  is the minimum mean free path for such scattering (see, for example, Refs [5, 40]). However, this contradiction is resolved if it is remembered that estimate (19) refers primarily to the phonons traveling along the axis of the waveguide, whereas the restriction  $l_{\rm ph} = D$  refers to those traveling at arbitrary (including large) angles to the axis. But it is exactly the axially traveling longitudinal phonons that make the most contribution to the nanowire thermal conductivity due to the largest projection of the group velocity  $V_{phz}$  on the axis of the quasi-onedimensional sample [see formula (20)]. Applying estimate (19) primarily to the axially propagating phonons also removes the 'quasi-one-dimensionality' restriction on nanowire phonons, i.e., the requirement  $k_{ph}D < 1$  (where  $k_{ph}$  is the wave number of a thermal phonon) which is met only at very low temperatures, even in nanowires with an average diameter of 100 nm ( $\approx 200a$ ) [5]. On the other hand, when the parameter  $a/\delta$  becomes very small with increasing rootmean-square roughness height, it should be remembered that the phonon mean free path (19) cannot be less than half the phonon wavelength  $\lambda_{ph}/2$  (see Ref. [41]). Therefore, in nanowires with small enough diameters and rough surfaces the phonon mean free path can tend to  $\lambda_{\rm ph}/2$ , while the phonon thermal conductivity to the lower limit of thermal conductivity for an amorphous solid. The fact that the thermal conductivity of nanowires made of single-crystal silicon tends to the limiting value of the thermal conductivity of amorphous silicon as the diameter of a rough surface nanowire decreases was also discovered (but not explained) in Ref. [5].

To summarize, the proposed mechanism of nonresonant phonon scattering from surface phonon leads that model the dynamic surface roughness of a phonon waveguide allowed us to explain, qualitatively and in part quantitatively, the significantly (almost by an order of magnitude) reduced thermal conductivity of rough-surface, compared to smooth-surface, nanowires, as well as to suggest the reason why nanowires of single-crystal materials achieve the lower limit of thermal conductivity found in an amorphous solid. The important point here is that the 'parallel dynamic connection' of an ideal heat conductor (crystalline phonon waveguide) with a poor heat conductor (disordered surface lattice layer) leads to a marked reduction in the thermal conductivity of the composite as a whole-unlike the electric conductivity of parallel-connected ideal (for example, superconducting) and resistive electric conductors.

## 4. Multichannel photon scattering from two-dimensional nanostructures

The idea of multichannel propagation may find another application to the scattering of photons from two-dimensional systems. Similarly to acoustic phonons, an additional propagation channel can result in a photon being totally reflected from a two-dimensional system with a physical thickness much smaller than the incident wavelength. Reference [23] gives examples of various anisotropic and/or gyrotropic 2D systems that scatter a photon such that it undergoes total reflection or total polarization conversion. The simplest system of this type is a thin layer of a polar, cubic GaAs type semiconductor whose characteristic frequency dispersion of the dielectric constant,  $\varepsilon_{ik} = \varepsilon \delta_{ik}$ , is due to optical phonons [42]:

$$\varepsilon = \varepsilon_{\infty} + \frac{\varepsilon_0 - \varepsilon_{\infty}}{1 - \omega^2 / \omega_{\rm TO}^2 - i\Gamma \omega / \omega_{\rm TO}^2} , \qquad (21)$$

where  $\varepsilon_0$  and  $\varepsilon_{\infty} < \varepsilon_0$  are the static and optical dielectric constants, and  $\omega_{\rm TO}$  and  $\Gamma$  are the frequency and the attenuation constant of a long-wave transverse optical phonon. It is a simple matter to see [see formulas (22) and (23) and Fig. 6] that close to the frequency  $\omega_{TO}$ , at which  $\varepsilon \to \infty$ , a resonant increase occurs in the reflection coefficient from a thin layer at the interface between two media (including the case in which such a layer resides in a vacuum). In this case, the reflection curve is generally asymmetric as a function of frequency (see Fig. 6). The increase in the reflection coefficient at resonance is greater, the higher the quality factor [which is described by the parameter  $\omega_{\rm TO}/\Gamma$  in formula (21)] of the optical phonon is. However, if the thin semiconductor layer is at the interface of two identical media (for example, in a vacuum), then for  $\varepsilon(\omega) = 1, \, \omega > \omega_{\rm TO}$  the photon undergoes total transmission through the layer. The asymmetric shape of the transmission coefficient through a thin layer of a polar semiconductor can be related to the interference of two photon paths: through a resonance with an optical phonon, and through the surrounding medium with dielectric constant  $\varepsilon_{\infty}$ , i.e., with the Fano effect for photons.



**Figure 6.** Energy reflection coefficient as a function of normalized frequency for a photon incident on a 100-nm-thick layer of polar GaAs semiconductor at the vacuum–glass interface;  $\omega_{TO}$  is the frequency of a transverse optical phonon. The remaining layer parameters are given in the text.

Another photon analogue of the Fano effect is presented by the interaction of photons with a two-dimensional metaldielectric type nanostructure consisting, for example, of single or double strips of 2D electron gas on a substrate of a GaAs type semiconductor [43], or of resonant metallic elements like split double [44, 45] or single [46] ring cavities on glass substrates. Resonantly enhanced photon reflection from such structured (laterally nonuniform) 2D electronic systems is observed in the far infrared [43, 44] and in the optical range with  $v \approx 100$  THz [45, 46]. Common to all of these structured two-dimensional electronic systems (STDESs) is the fact that photons interact with local electronic nanostructures (LENSs) located at a certain concentration on a transparent substrate and exhibiting local electron - plasmon resonances. This suggests that a resonant reflection enhancement can be related to the destructive interference of two photon paths: through a local electron-plasmon resonance, and through the transparent substrate surrounding the resonator.

Macroscopically, the interaction of a photon with a 2D system is described in the general case in terms of the effective dynamic conductivity  $\sigma_{\alpha\beta}(\omega)$ ,  $\alpha, \beta = 1, 2$  of the 2D system, which relates the surface (dynamic) current to the electric field component tangent to the surface (see, for example, Refs [23, 47]. For a photon normally incident from medium 1 to medium 2 with respective refraction indices  $n_1$  and  $n_2$ , the following expressions can be obtained for the amplitude coefficients of reflection ( $r^{(x,y)}$ ) and transmission ( $t^{(x,y)}$ ) for the photon electric field polarized along the *x*- or *y*-axis, respectively, in the plane of the 2D system:

$$r^{(x,y)} = \frac{n_1 - n_2 - (4\pi/c) \,\sigma_{xx,yy} + \frac{\left[(4\pi/c) \,\sigma_{xy}\right]^2}{n_1 + n_2 + (4\pi/c) \,\sigma_{yy,xx}}}{n_1 + n_2 + (4\pi/c) \,\sigma_{xx,yy} - \frac{\left[(4\pi/c) \,\sigma_{xy}\right]^2}{n_1 + n_2 + (4\pi/c) \,\sigma_{yy,xx}}},$$
$$t^{(x,y)} = 1 + r^{(x,y)}, \qquad (22)$$

where *c* is the speed of light in vacuum. Equation (22) also describes the possible anisotropy and/or gyrotropy of the 2D electronic system, which in the general case are introduced through the different diagonal ( $\sigma_{xx}$  and  $\sigma_{yy}$ ) and the off-diagonal ( $\sigma_{xy}$ ) components of the 2D conductivity tensor  $\sigma_{\alpha\beta}$ . The dynamic 2D conductivity tensor  $\sigma_{\alpha\beta}(\omega)$ can, in the general case, be related to the 'excess' local dielectric susceptibility tensors ( $\varepsilon_{\alpha\beta}(\omega) - \varepsilon^{(1)}\delta_{\alpha\beta}$ )/4 $\pi$  in the thin layer of thickness *d* and average dielectric susceptibility tensor at the interface of two (isotropic) media 1 and 2, ( $\bar{\varepsilon} - \varepsilon^{(1)}$ )  $\delta_{\alpha\beta}/4\pi$ ,  $\bar{\varepsilon} = (\varepsilon^{(1)} + \varepsilon^{(2)})/2$ , with respect to the susceptibility of medium 1 (with lower dielectric constant,  $\varepsilon^{(1)} \leq \varepsilon^{(2)}$ ):

$$4\pi\sigma_{\alpha\beta} = -i\omega d \left[ \varepsilon_{\alpha\beta} + \left( \frac{\varepsilon^{(2)}}{2} - \frac{3}{2} \varepsilon^{(1)} \right) \delta_{\alpha\beta} \right], \tag{23}$$

where it is assumed that  $\omega d/c \ll 1$ .

Figure 6 depicts the frequency dependence of the energy reflection coefficient of a photon (incident normally from a vacuum) from a GaAs layer of thickness d = 100 nm located at a vacuum–glass interface. The calculations performed used formulas (21)–(23) with the following values of GaAs parameters:  $\varepsilon_0 = 12.9$ ,  $\varepsilon_{\infty} = 10.9$ ,  $\omega_{\text{TO}} = 2\pi \times 8$  THz,  $\Gamma = 0.77 \times 10^{12} \text{ s}^{-1}$ , and with  $\varepsilon^{(2)} = 2.25$  for glass. As seen from the figure, at resonance with a transverse optical phonon

a large increase from 4% to 33% indeed occurs in the reflection coefficient of a T-photon from a nano-thickness layer of a polar semiconductor (the photon wavelength in vacuum is 375 times the film thickness!). For a photon reflected from the same GaAs layer in a vacuum, the energy reflection coefficient varies from essentially zero out of resonance to 28% at resonance ( $\omega = \omega_{TO}$ ). It should be noted that calculations based on formulas (21)–(23) agree to a high accuracy with those using expressions for *R* and *T* known from the optics of layered media (see Ref. [29]), with the same GaAs layer parameters.

For an STDES at the interface of two media, in the presence of a perpendicular magnetic field B, the following expressions can be obtained for the components of the 2D conductivity tensor [23]:

$$\sigma_{xx,yy} = i \left[ \frac{n_{s}e^{2}\omega}{m_{xx,yy}^{*}(\omega^{2} - \omega_{c}^{*2})} - \frac{1}{4\pi} \left( \overline{\varepsilon} - \varepsilon^{(1)} \right) \omega d^{*} \right], \quad (24)$$

$$\sigma_{xy} = -\sigma_{yx} = \frac{n_{\rm s} e^2 \omega_{\rm c}^*}{\sqrt{m_{xx}^* m_{yy}^*} (\omega^2 - \omega_{\rm c}^{*2})} , \qquad (25)$$

$$m_{xx,yy}^* = m^* \left[ 1 - \frac{\omega_{0x,y}^2}{\omega^2} + \frac{i\gamma}{\omega} \right], \qquad (26)$$

$$\omega_{0x,y}^2 = \frac{2\pi^2 \tilde{n}_{\rm s} e^2}{\bar{\epsilon} m^* W_{x,y}}, \quad n_{\rm s} = n_{\rm ds} N_{\rm d} = n_{\rm ds} \tilde{n}_{\rm s} W_x W_y, \qquad (27)$$

$$\omega_{\rm c}^* = \frac{eB}{c\sqrt{m_{xx}^*m_{yy}^*}},\tag{28}$$

where  $\omega_{0x,y}$  are the frequencies of local electron-plasmon resonances,  $\gamma$  is the electron scattering rate in an LENS,  $\omega_c^*$ is the effective cyclotron frequency,  $m^*$  is the effective carrier mass in an LENS,  $n_s$  is the average electron surface density in the two-dimensional structure,  $n_{ds}$  is the number of LENSs per unit area,  $N_d = \tilde{n}_s W_x W_y$  and  $\tilde{n}_s$  are the number of electrons and the average electron number density in one LENS, respectively,  $W_{x,y}$  are the characteristic sizes of a (rectangular) LENS, and  $d^*$  is the effective thickness of the two-dimensional system (in the case of a bilayer LENS [43, 45]).

Because the two-dimensional dynamic conductivity of an STDES, formula (24) with B = 0, has a frequency dependence similar to that of the two-dimensional layer of a polar semiconductor, Eqns (21) and (23), it follows from formulas (22)-(27) that in the absence of an external magnetic field the resonant reflection from an STDES similar to that shown in Fig. 6 should be observed near each of the local electron – plasmon resonances. The spectral position, depth, and width of such a resonance are determined by the values of the parameters  $\omega_{0x, y}$  and  $\gamma$ , and also by the average electron surface density  $n_{\rm s}$  which determines the effective 'oscillator strength' of the resonance. In particular, the two-dimensional concentration of LENSs influences only the depth and width, but not the spectral positions of transmission minima (reflection maxima) [46]—a fact which Eqns (22)-(27) do incorporate because reducing the two-dimensional concentration of LENSs results in decreasing the oscillator strength  $n_{\rm s}$  virtually without changing its resonance frequency  $\omega_{0x,y}$ and the damping parameter  $\gamma$ . In the limit of zero damping of optical phonons (or electrons) in the local structure, the conditions  $r^{(x,y)} = -1$ ,  $t^{(x,y)} = 0$  should be satisfied at a reflection resonance for the arbitrarily small (down to monatomic) physical thickness d (or  $d^*$ ) of the 2D system (23) or (24).

On the other hand, formulas (22) suggest that in the case of  $\sigma_{xx,yy} = 0$  (and  $\sigma_{xy} = 0$ , B = 0) an STDES at the boundary of dissimilar media with  $\varepsilon^{(1)} < \varepsilon^{(2)}$  becomes optically transparent for a photon with appropriate polarization. The photon transmission and reflection coefficients are the same as at the interface of media 1 and 2 without a 2D electronic system. Reference [48] described the total transmission of a photon through a thin semiconductor layer made of highpermittivity material and containing a two-dimensional electron gas. In the recent paper [49], a similar phenomenon of a 'totally transparent structured film' was discovered experimentally in the optical range in a two-dimensional square lattice fabricated from pairs of cylindrical gold posts  $\approx 80$  nm in height placed on a glass substrate. Within the framework of Eqns (22)–(28) and expression (24) for  $\sigma_{xx,yy}$ , this phenomenon can be described, for example, by taking  $\sigma_{xx} = 0, d^* \sim 80 \text{ nm}, \bar{\epsilon} - \epsilon^{(1)} \approx 0.63 \text{ (vacuum - glass inter$ face),  $m^* = m_e$ , B = 0, and the corresponding values of the electron – plasmon resonance frequency  $\omega_{0x}$ , electron scattering parameter  $\gamma$ , and the average electron surface density  $n_{\rm s}$ .

The essential point is that to explain the experimental results of Ref. [49] in terms of Eqns (22)–(28) and using the photon analogy of the Fano effect, there is no need to introduce (as in Ref. [49]) negative permeabilities  $\mu(\omega)$  in the optical frequency range. In Ref. [49] and also in Refs [44-46], the negative values of permeability in the optical frequency range were used to explain the resonant enhancement in photon reflection from STDESs. (In this connection, interestingly, earlier references on the reflection of electromagnetic waves from STDESs [43] did not use negative permeabilities of the system to explain experiments.) Indeed, Eqns (22) - (28)assume that the permeability of a nonmagnetic STDES (including when in an external magnetic field) is identically equal to unity. These equations can also be used to describe the resonant enhancement in photon reflection from an STDES (see Fig. 6). (According to formulas (23), (24), and (27), coating a 2D system of pairs of nanoposts with a thin layer of glycerine of thickness  $d^{(3)} \sim d^*$  and with  $\varepsilon^{(3)} > 1$  [49] increases the average effective dielectric constant  $\bar{\varepsilon}$  at the interface and lowers the frequency  $\omega_{0x}$  of the reflection resonance from an STDES-which is exactly what the experiments in Ref. [49] showed.) Moreover, in accordance with the estimates given by Landau and Lifshitz [50] and discussed in Ref. [49], taking into account the deviation of  $\mu(\omega)$  from unity in the optical and higher-frequency ranges is "clear excess of accuracy". Therefore, an important conclusion of this section is that the resonant enhancement in photon reflection from STDESs found experimentally in the optical frequency range can be explained by and reproduced with equations like (22)-(28) under the assumption of the permeability of the system being identically equal to unity,  $\mu(\omega) = 1$ , which is fully consistent with the statement in Ref. [50] concerning the permeability of materials in the optical (and higher) frequency range.

Interest in media with negative permeability  $\mu(\omega)$  was sparked by the prediction made by Veselago [51] that *isotropic material* with both negative  $\varepsilon$  and  $\mu$  should have a negative refraction index  $n = \sqrt{\varepsilon \mu}$ , the underlying reason being that in such a material the Poynting vector  $\mathbf{P} = (c/4\pi) \mathbf{E} \times \mathbf{H}$  is antiparallel to the photon wave vector  $\mathbf{k}$ . Additional interest in these unusual materials was created by the suggestion put forward in Ref. [52] that the materials with negative refraction indices could be used to fabricate 'perfect lenses'—lenses whose resolving power is not limited by the wavelength of the photon and which are therefore of much interest. Because materials with such properties do not exist in nature - not as far as optical wavelengths are concerned - extensive efforts have been made to produce artificial materials with both  $\varepsilon$  and  $\mu$  being negative [53]. But, as noted above when mentioning the estimate and statement in the book [50], the predicted existence of materials with negative  $\mu$  in the optical (and higher) frequency range is theoretically inconsistent. On the other hand, no known theoretical framework is at odds with the existence of anisotropic materials in which the Poynting vector is not along (or is even antiparallel to) the photon wave vector in a certain frequency range (and in a certain interval of directions) (see, for example, Ref. 54]). Understanding the refraction of waves in such media can be greatly enhanced by analyzing the geometry of the 'isofrequency surface' of elementary excitations propagating in an anisotropic medium. One example is given in Ref. [55], in which the amplitude damping of an elastic surface wave in the bulk of an anisotropic crystal is related to the presence of nonconvex portions at the isofrequency surface of crystal phonons with appropriate polarization. Section 5 below briefly describes a simple periodic, anisotropic, acoustic system negatively refracting for a certain acoustic frequency range and suggests some simple experiments in which this property can be observed. The essential point here is that such a periodic anisotropic system can be fabricated either from macroscopic or nanoscale structural elements.

### 5. Negative refraction of phonons in periodic anisotropic media and the acoustic analogue of the Fano effect

Let us consider a simple two-component acoustic superlattice consisting of plane layers of materials A and B. The propagation of phonons in a periodic medium can be described on the basis of the Bloch waves, in which a wave is characterized by the Bloch wave vector **k**, frequency  $\omega$  and group velocity V<sub>ph</sub>. In the quasiclassical approximation, these wave characteristics can change adiabatically in time and space, and in doing so obeying the following equations (see, for example, Ref. [56]):

$$\dot{\mathbf{k}} = -\nabla \omega, \quad \mathbf{V}_{\mathrm{ph}} = \frac{\partial \omega}{\partial \mathbf{k}},$$
(29)

where the frequency  $\omega$  determines the phonon energy  $E_{\rm ph} = \hbar \omega$  and is therefore assumed to be positive.

As follows from equations (29), the directions of the phonon group velocity and the corresponding Poynting vector are determined by the direction of the (outer) normal to the phonon isofrequency surface  $\omega = \text{const.}$  Using the results of Ref. [57] on the propagation of waves at an arbitrary angle to an axis of an acoustic superlattice, it is possible to prove that in a two-component acoustic superlattice formed by layers of thicknesses  $d_A$  and  $d_B$  of materials with very different acoustic impedances ( $\rho_A c_A \ll \rho_B c_B$ , where  $\rho_{A,B}$  and  $c_{A,B}$  are the density and velocity of the sound of the appropriate polarization in layers A and B), in the case of  $c_A/d_A = c_B/2d_B$  the second miniband has a small width and a negative group velocity along the Z-axis of the superlattice:

$$\omega^{2} = c_{A}^{2} k_{x}^{2} + \left[ \pi \frac{c_{A}}{d_{A}} + 2 \frac{c_{A}}{d_{A}} \frac{\rho_{A} c_{A}}{\rho_{B} c_{B}} \cos(k_{Z} d) \right]^{2}, \ d = d_{A} + d_{B},$$
(30)

Such a relatively narrow miniband is found, for example, in a simple acoustic superlattice formed by Plexiglass layers periodically arranged in water (in which case A and B in formulas (30)-(31) stand for water and Plexiglass, respectively). In a perturbed acoustic Plexiglass – water superlattice, temporal *acoustic Bloch oscillations* in the ultrasound transmission coefficient through the superlattice layer were observed for the first time, similar to electron Bloch oscillations found in a semiconductor superlattice in an external electric field [58]. The perturbation of the acoustic superlattice was achieved by a water layer thickness gradient—leading, in accordance with Eqns (29) and (31), to temporal oscillations in the group velocity (and hence in the acoustic Poynting vector) along the superlattice axis:

$$V_{\rm ph\,Z} \approx 2c_{\rm A}\,\frac{d}{d_{\rm A}}\,\frac{\rho_{\rm A}c_{\rm A}}{\rho_{\rm B}c_{\rm B}}\sin(\omega_{\rm B}t)\,,\tag{32}$$

where the frequency  $\omega_{\rm B} = |d\partial\omega_{\rm cav}/\partial Z| \approx |\pi(c_{\rm A}/d_{\rm A}^2)\partial d_{\rm A}/\partial z|$ of acoustic Bloch oscillations is determined by a small gradient of central resonance frequencies of 'water cavities' between neighboring Plexiglass layers,  $\omega_{\rm cav} = \pi c_{\rm A}/d_{\rm A}$  [see formula (30)].

Because an unperturbed anisotropic periodic system has a frequency interval for waves with negative group velocity along the superlattice axis — the length of the interval being equal to the width  $2\Delta = 4\rho_A c_A^2/(\rho_B c_B d_A)$  of the acoustic miniband (30) near the central resonance frequency  $\omega_{cav}$  — this simple system makes it possible for ultrasonic acoustic waves to undergo negative refraction and to have a negative refraction index. Some aspects of negative refraction of acoustic waves have been studied in acoustical crystals that are more difficult to make, consisting of a two-dimensional lattice of solid cylinders in the air (see Ref. [59] and references cited therein).

Negative refraction in the three-dimensional layered system under consideration can be conveniently explained by constructing the isofrequency surface of acoustic oscillations using Eqn (30). Figure 7 displays the cross section of this surface by the  $k_x k_z$  plane for the parameters of the water – Plexiglass superlattice that were used in the experiments:  $d = 2d_A$ ,  $\rho_A c_A / (\rho_B c_B) = 0.47$ , and  $\omega = 1.15\omega_{cav}$  [58]. (A miniband with such an isofrequency surface occurs for  $\omega > \omega_{cav} - \Delta$ , and for  $\omega > \omega_{cav} + \Delta$  the isofrequency surfaces shown in Fig. 7 transform into a single open surface in the form of a  $k_z$ -aligned 'corrugated cylinder'—a Fermi surface shape known from the theory of metals [60].) In accordance with the laws of radiation, the group velocity of an acoustic wave incident normally to the layers should be directed inward with regard to the superlattice, whereas its wave vector will, according to Eqn (31) and Fig. 7, be directed oppositely, i.e., away from the superlattice. Therefore, if the second edge of the superlattice is cut, making it wedgeshaped, then the acoustic wave going out from the opposite side will be refracted at a negative angle to the external medium. The same phenomenon of negative refraction of electromagnetic waves in microwave range (10 to 12 GHz) was studied in Refs [61, 62] in much more complex wedgeshaped structures with a 'high density of wires'. The discovery and study of negative acoustic refraction in simple layered



**Figure 7.** Isofrequency surface of longitudinal ultrasound waves in an acoustic water–Plexiglass superlattice. The frequency and normalized parameters of the superlattice are given in the text.

water – solid systems is potentially of both fundamental and applied interest. It is essential that a composite medium for the study of acoustic Bloch oscillations and negative refraction can be made both of macroscopic elements (like layers of a solid material in water) and of nanoscale structural elements (like the semiconductor superlattice with 'acoustic nanocavities' designed in Ref. [1]).

Negative group velocity of waves propagating along an axis of superlattice (31) in miniband (30) will also be encountered in studying acoustic Bloch oscillations in a perturbed superlattice similar to that considered in Ref. [58] but for a different arrangement of the experiment. What needs to be monitored in this new arrangement is the transverse oscillations of a Gaussian beam (with a finite width across layers) propagating along the layers of a perturbed superlattice. A similar arrangement of the experiment was used, for example, in Ref. [63], which studied the transverse Bloch oscillations of an optical Gaussian beam in a two-dimensional system of parallel waveguides with a transverse gradient of refraction indices of individual waveguides (the gradient being due to a transverse gradient in temperature). In the experiments of Ref. [63], a Gaussian beam excited by a laser at the ends of several waveguides periodically shifted to the region of a higher index of refraction as it propagated, the reason being that optical excitations have a positive group velocity along the axis of the unperturbed superlattice. However, in the case of miniband (30) with a negative group velocity (31) along the axis of the unperturbed acoustic superlattice, a Gaussian beam of ultrasound waves which is excited at the ends of several layers will, as it propagates, shift periodically to the region of a lower index of refraction, i.e., to that region of a perturbed superstructure where water layers between Plexiglass layers are thinner. The Bloch oscillations of the transverse shift of the ultrasound Gaussian beam can be visualized.

A further possible source of a narrow acoustic miniband with a negative group velocity along an axis of a superlattice is an analogue of the Fano effect for acoustic waves in the case in which relatively thin layers of a solid material have holes (with a diameter of about the thickness of the layer) forming identical two-dimensional lattices, square or rectangular, in all the layers of the water-solid superlattice. If the lattice constant a of the two-dimensional lattice of holes exceeds the thickness of the solid material layer, then there is a possibility for a normally incident longitudinal wave to be resonantly reflected from an individual thin layer due to the destructive interference of two acoustic paths: through the resonant oscillations of standing bending waves in a perforated layer (with in-layer wave number  $\approx \pi/a$ ), and through the 'averaged' solid material layer. Resonant reflection from a relatively thin perforated layer of a solid material in water will have a line shape similar to that shown in Fig. 6. But if solid material layers with identical two-dimensional lattices of holes form a superlattice and if the narrow transmission resonance falls within the first forbidden band of the superstructure (this position of the resonance of acoustic waves with the bending oscillations of the cylinder shape is investigated in Ref. [33] for a two-dimensional lattice of thin-walled cylinders in a gas or a liquid), then such a resonance can produce in the superlattice a narrow miniband for wave propagation with negative dispersion of the group velocity along a superlattice axis (because such a miniband will be the closest to the acoustic band with the positive dispersion). In this case, the acoustic waves that enter into resonance with the narrow miniband undergo negative refraction when passing through a wedge-shaped sample of such acoustic 'metamaterial'. The resonant reflection effect was first discovered in a study of photon propagation through layers of a transparent material with a two-dimensional lattice of holes [25, 26]. By analyzing the isofrequency surface of phonons or photons in anisotropic periodic systems whose structural elements show the Fano effect, it is possible to explain the origin of negative acoustic or electromagnetic wave refraction in such media.

### 6. Conclusion

Let us summarize the main points of this report. (1) A description is given for a theory developed for the phonon analogue of the Fano effect, which is predicted for the first time and is observed in low-dimension multichannel systems, in particular, in 'locally resonant' media. (2) A simple model is proposed for an additional channel of transmission of longwavelength phonons through a crystal two-dimensional defect or a quasi-one-dimensional phonon nanowaveguide. How and when an additional transmission channel for acoustic phonons can lead to the total resonant reflection or absorption of phonons is analyzed. (3) It is shown that the nonresonant interaction of acoustic phonons with the dynamically rough surface of a nanowaveguide markedly reduces the mean free path of phonons in such lowdimension structures. The predicted reduction in phonon mean free path and phonon thermal conductivity of nanowires is in agreement with experimental data on thermal conductivity of silicon nanowires with smooth and rough surfaces. (4) It is shown that the multichannel propagation and scattering of photons can lead to an observed enhancement in reflection from thin layers of polar semiconductors and two-dimensional structured electronic systems on a transparent substrate. Introducing the multichannel scattering of photons in a two-dimensional structured electronic

system makes it possible in some of the cases studied to avoid using the negative permeability at optical frequencies. (5) It is shown that analysis of phonon or photon isofrequency surfaces in macroscopically or nanoscale periodic structures makes it possible to explain the origin of the negative refraction of acoustic and electromagnetic waves in such media and to predict new observable effects.

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#### References

- 1. Huynh A et al. Phys. Rev. Lett. 97 115502 (2006)
- 2. Stroscio M A et al. J. Phys.: Condens. Matter 8 2143 (1996)
- 3. Feher A et al. Fiz. Nizk. Temp. **31** 1211 (2005) [Low Temp. Phys. **31** 921 (2005)]
- 4. Li D et al. Appl. Phys. Lett. 83 2934 (2003)
- 5. Hochbaum A I et al. *Nature* **451** 163 (2008)
- 6. Boukai A I et al. Nature 451 168 (2008)
- 7. Padgett C W, Shenderova O, Brenner D W Nano Lett. 6 1827 (2006)
- 8. Fano U Phys. Rev. 124 1866 (1961)
- Sánchez I, Martin F Phys. Rev. A 49 5116 (1994); J. Phys. B: At. Mol. Opt. Phys. 27 4105 (1994)
- 10. Piao G et al. Solid State Commun. 75 835 (1990)
- 11. Cerdeira F, Fjeldly T A, Cardona M Phys. Rev. B 8 4734 (1973)
- 12. Tejedor C et al. Phys. Rev. B 32 5303 (1985)
- 13. Bellani V et al. Semicond. Sci. Technol. 11 1411 (1996)
- 14. Faist J et al. *Nature* **390** 589 (1997)
- 15. Göres J et al. Phys. Rev. B 62 2188 (2000)
- 16. Zacharia I G et al. Phys. Rev. B 64 155311 (2001)
- 17. Kim J et al. Phys. Rev. Lett. 90 166403 (2003)
- 18. Johnson A C et al. Phys. Rev. Lett. 93 106803 (2004)
- 19. Sato M et al. Phys. Rev. Lett. 95 066801 (2005)
- 20. Kobayashi K et al. Phys. Rev. Lett. 88 256806 (2002)
- 21. Nakanishi T, Terakura K, Ando T Phys. Rev. B 69 115307 (2004)
- 22. Hofstetter W, König J, Schoeller H Phys. Rev. Lett. 87 156803 (2001)
- 23. Kosevich Yu A Solid State Commun. 104 321 (1997)
- 24. Gantzounis G, Stefanou N Phys. Rev. B 72 075107 (2005)
- 25. Fan S, Joannopoulos J D Phys. Rev. B 65 235112 (2002)
- 26. Suh W, Solgaard O, Fan S J. Appl. Phys. 98 033102 (2005)
- 27. Kosevich Yu A Prog. Surf. Sci. 55 1 (1997)
- 28. Fellay A et al. Phys. Rev. B 55 1707 (1997)
- Brekhovskikh L M Volny v Sloistykh Sredakh (Waves in Layered Media) (Moscow: Izd. AN SSSR, 1957) [Translated into English (New York: Academic Press, 1960)]
- 30. Liu Z et al. Science 289 1734 (2000)
- 31. Goffaux C et al. Phys. Rev. Lett. 88 225502 (2002)
- 32. Goffaux C, Sánchez-Dehesa J Phys. Rev. B 67 144301 (2003)
- Kosevich Yu A, Goffaux C, Sánchez-Dehesa J Phys. Rev. B 74 012301 (2006)
- Landau L D, Lifshitz E M *Teoriya Uprugosti* (Theory of Elasticity) (Moscow: Nauka, 1987) [Translated into English (Oxford: Pergamon Press, 1986)]
- Andreev A F, Kosevich Yu A Zh. Eksp. Teor. Fiz. 81 1435 (1981) [Sov. Phys. JETP 54 761 (1981)]
- Kosevich Yu A, Syrkin E S Fiz. Tverd. Tela 33 2053 (1991) [Sov. Phys. Solid State Phys. 33 1156 (1991)]
- 37. Dunlap D H, Wu H-L, Phillips P W Phys. Rev. Lett. 65 88 (1990)
- 38. Phillips P, Wu H-L Science 252 1805 (1991)
- 39. Kent A J et al. Phys. Rev. Lett. 96 215504 (2006)
- 40. Mingo N et al. Nano Lett. 3 1713 (2003)
- 41. Cahill D G, Watson S K, Pohl R O Phys. Rev. B 46 6131 (1992)
- 42. Born M, Huang K Dynamical Theory of Crystal Lattices (Oxford:
- Clarendon Press, 1954) [Translated into Russian (Moscow: IL, 1958)]
- 43. Demel T et al. Phys. Rev. B 38 12732 (1988)
- 44. Yen T J et al. Science 303 1494 (2004)

- 45. Shalaev V M et al. Opt. Lett. 30 3356 (2005)
- 46. Linden S et al. *Science* **306** 1351 (2004)
- 47. Kosevich Yu A Zh. Eksp. Teor. Fiz. 96 353 (1989) [Sov. Phys. JETP 69 200 (1989)]
- Kosevich Yu A Pis'ma Zh. Eksp. Teor. Fiz. 53 143 (1991) [JETP Lett. 53 150 (1991)]
- 49. Grigorenko A N et al. Nature 438 335 (2005)
- Landau L D, Lifshitz E M *Elektrodinamika Sploshnykh Sred* (Electrodynamics of Continuous Media) (Moscow: Nauka, 1952) [Translated into English (Oxford: Pergamon Press, 1984)]
- Veselago V G Usp. Fiz. Nauk 92 517 (1967) [Sov. Phys. Usp. 10 509 (1968)]
- 52. Pendry J Phys. Rev. Lett. 85 3966 (2000)
- 53. Shalaev V M Nature Photon. 1 41 (2007)
- 54. Hoffman A J et al. Nature Mater. 6 946 (2007)
- Kosevich A M, Kosevich Yu A, Syrkin E S Zh. Eksp. Teor. Fiz. 88 1089 (1985) [Sov. Phys. JETP 61 639 (1985)]
- Landau L D, Lifshitz E M *Teoriya Polya* (The Classical Theory of Fields) (Moscow: Nauka, 1988) [Translated into English (Oxford: Pergamon Press, 1983)]
- 57. Kosevich Yu A, Syrkin E S Phys. Rev. B 43 326 (1991)
- Sanchis-Alepuz H, Kosevich Yu A, Sánchez-Dehesa J Phys. Rev. Lett. 98 134301 (2007)
- 59. Lu M-H et al. Nature Mater. 6 744 (2007)
- Lifshitz E M, Pitaevskii L M Fizicheskaya Kinetika (Physical Kinetics) (Moscow: Fizmatlit, 2001) [Translated into English (Oxford: Pergamon Press, 1981)]
- 61. Shelby R A, Smith D R, Schultz S Science 292 77 (2001)
- 62. Parazzoli C G et al. Phys. Rev. Lett. 90 107401 (2003)
- 63. Pertsch T et al. Phys. Rev. Lett. 83 4752 (1999)